

Silicon Carbide for Beam Monitoring and Ion FLASH Beams

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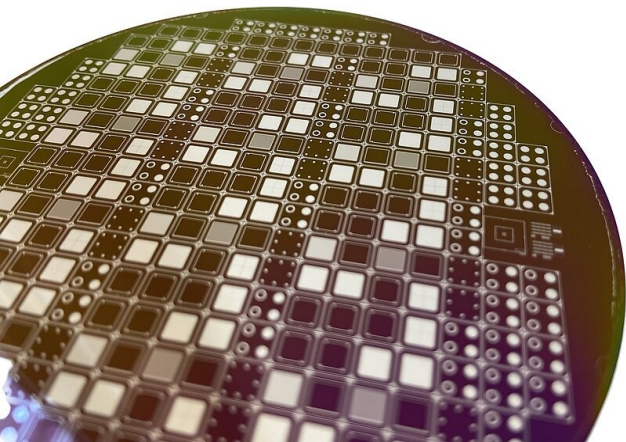
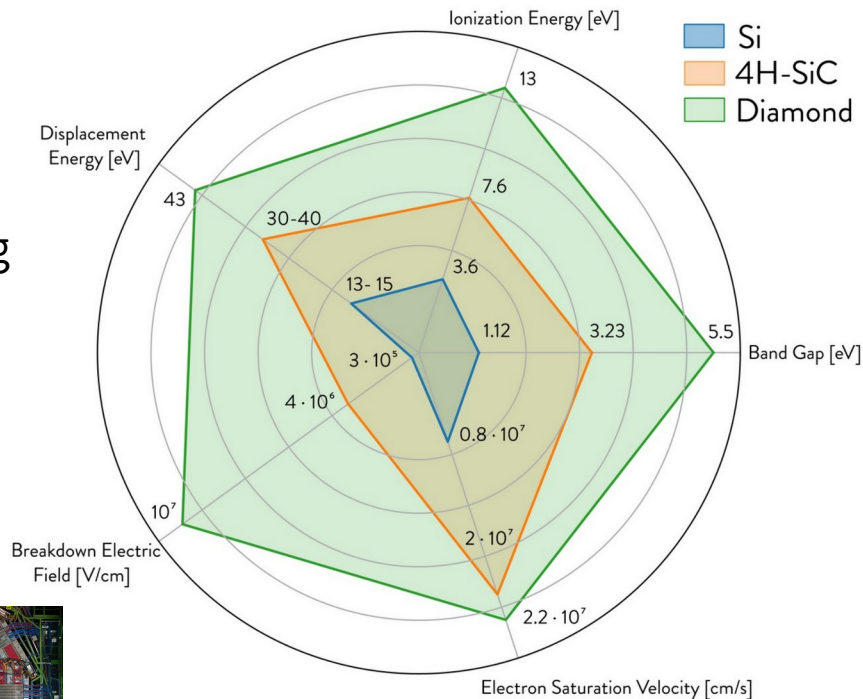


Silicon Carbide (SiC)

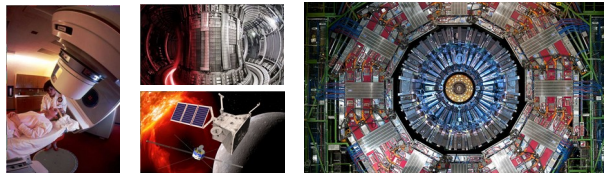
(4H)-Silicon Carbide is a wide bandgap semiconductor with many advantages:

- insensitive to visible light
- extremely low leakage currents ($< 1 \text{ pA/mm}^2$)
- Ability to work at high temperatures ($> 600 \text{ }^\circ\text{C}$)
- Higher breakdown field and drift velocity \rightarrow better timing

Drawbacks : Lower signal than Si, limitations on thickness



SiC Applications

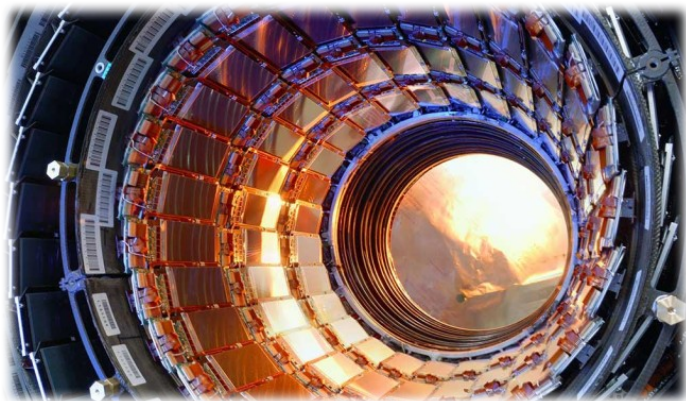


SiC Research at HEPHY

- SiC research ongoing at HEPHY since 2021
- Project together with MedAustron aiming to build a beam monitor,
 - based on SiC Strip detectors,
 - with a wide dynamic range : single particles to medical intensity

High Energy Physics

Timing, Radiation Hardness Studies



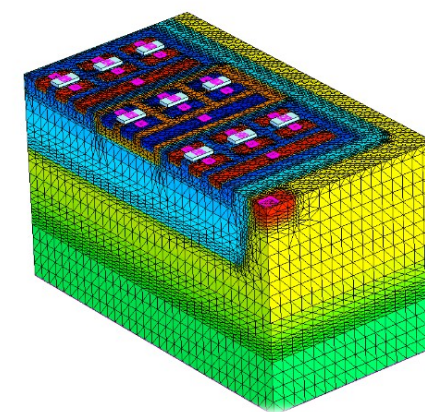
Medical Applications

Beam Monitoring, FLASH
Ion imaging (in the future)



Simulations

TCAD, Material Parameters
Design of novel detectors



FLASH RT with Ions

- Still not a lot of (pre-) clinical studies with p^+ FLASH beams (however, commercial availability of FLASH systems has increased a lot!)
- Carbon / helium beams only available at a few research / treatment centers

Take the first step and contribute to the implementation of FLASH beams at MedAustron

Extraction + **Instrumentation**



Elisabeth Renner (TU Wien)
Claus Schmitzer (MedAustron)

CONV-RT



FLASH-RT



FLASH Extraction

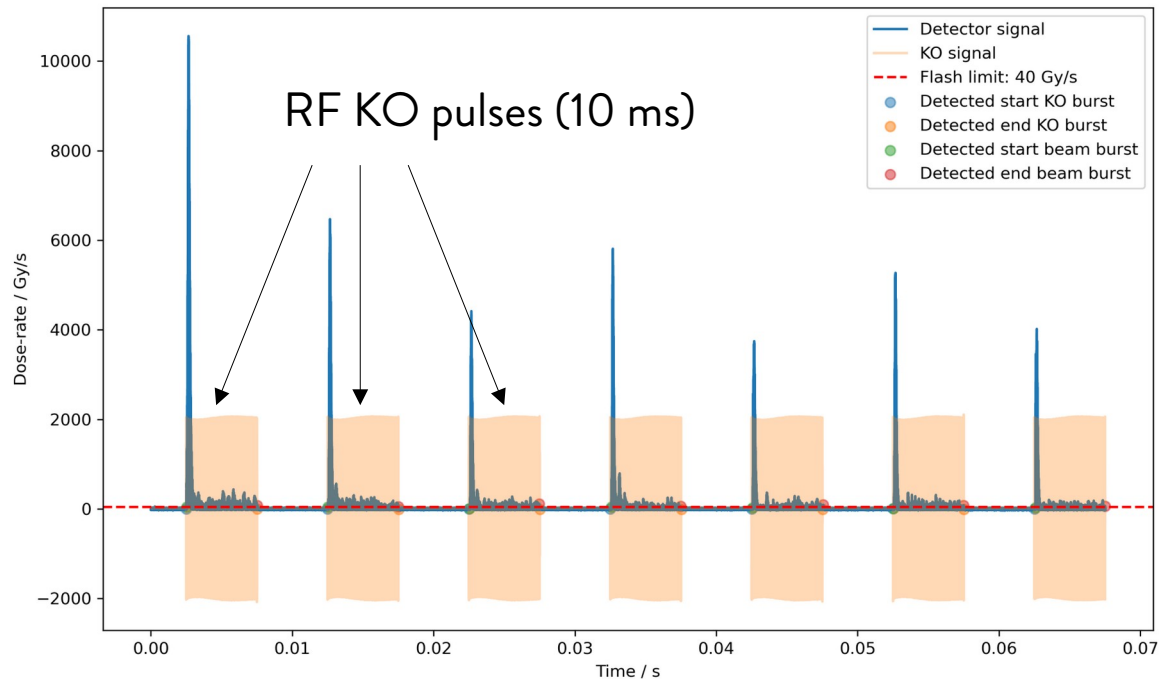
Many ways to extract a beam quickly:

- RF KO, PDE, COSE

Shown today : RF KO

- Horizontal excitation of beam, extracted by electrostatic septum
- Can be modulated: amplitude, phase, frequency
- Works very quickly (\sim MHz)

We are using *pulsed* RF KO



Why pulsed RF KO?

- Medical Device safety (*IEC 60601-2-64*): need to terminate irradiation in <0.25 Gy
- Single FLASH pulse (SPLASH) hard to implement safely

PAPER

[10.1088/1361-6560/ad5072](https://doi.org/10.1088/1361-6560/ad5072)

Pulsed RF knock-out extraction: a potential enabler for FLASH hadrontherapy in the Bragg peak

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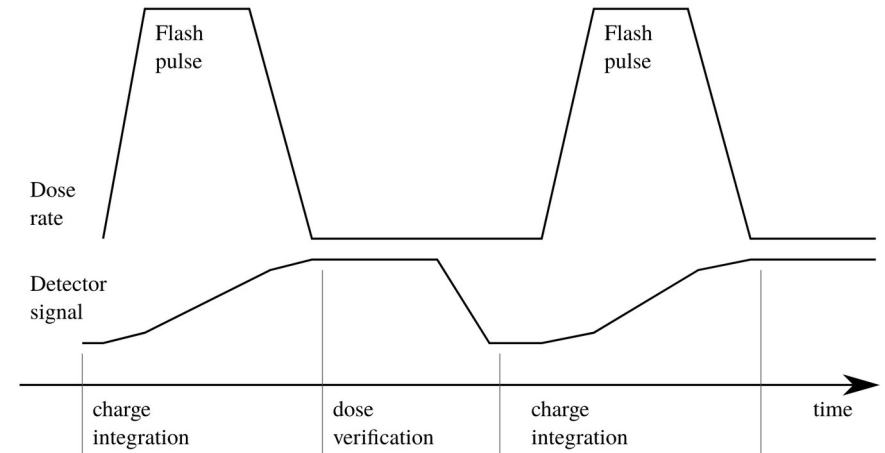
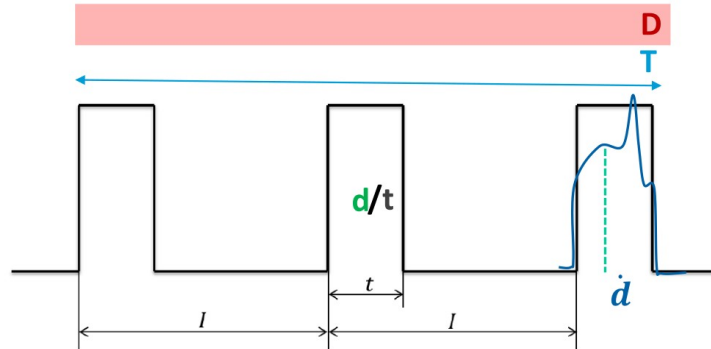
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Keywords: RFKO, FLASH, Hadrontherapy, Bragg-Peak

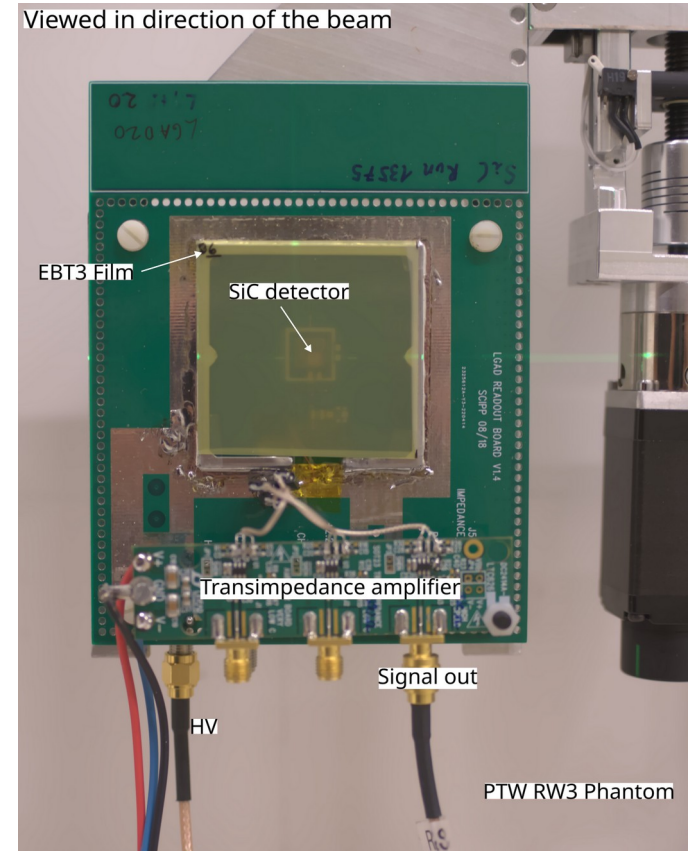
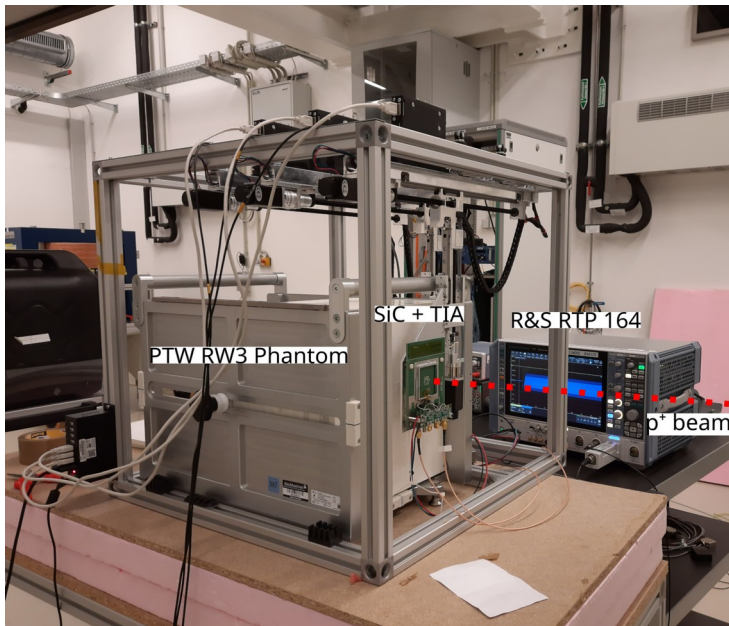
Customized beams for systematic FLASH studies:

- pulse length
- pulse separation
- dose per pulse



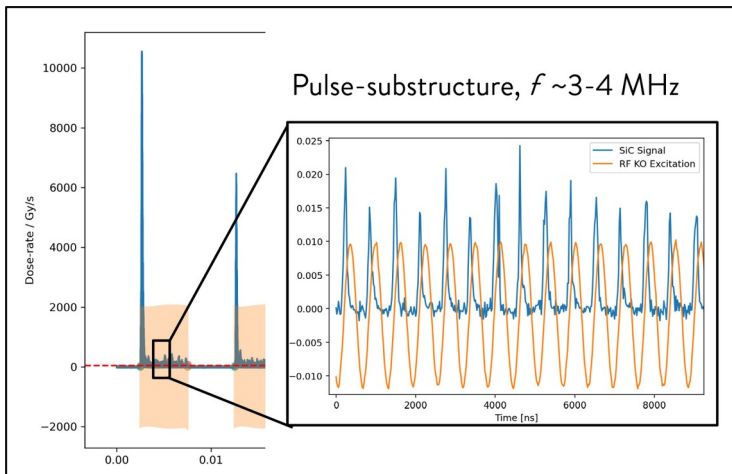
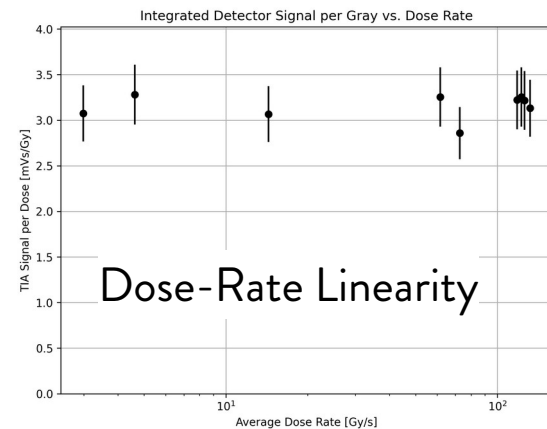
SiC Intensity Monitor

- $3 \times 3 \text{ mm}^2$ SiC diode with 50 μm thickness
- DC-coupled to transimpedance amplifier (Signal \propto dose rate) with 20 MHz bandwidth
- EBT3 films (IC and Bragg peak) for dose calibration

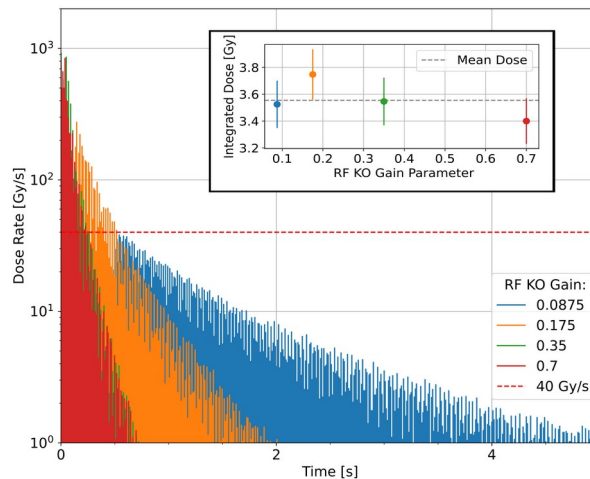


Selected RF KO FLASH Results

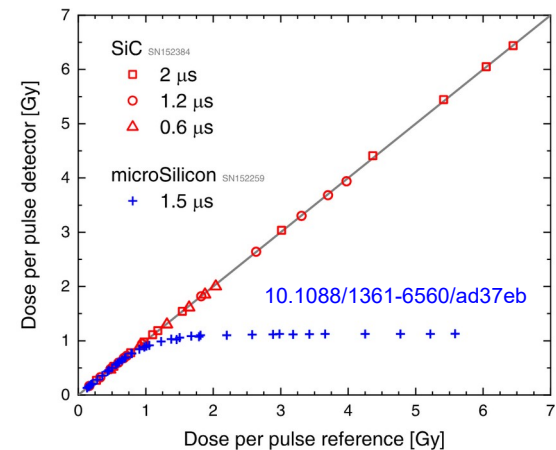
- Average dose rates of about 1 kGy/s can be reached (instantaneous dose even rate higher)
- Extremely good temporal resolution of beam intensity monitor (can observe individual RF KO cycle with 20 MHz bandwidth)
- No dose-rate dependencies / saturation observed for SiC detector



Temporal resolution of beam intensity monitor



Non-pulsed RF KO extraction



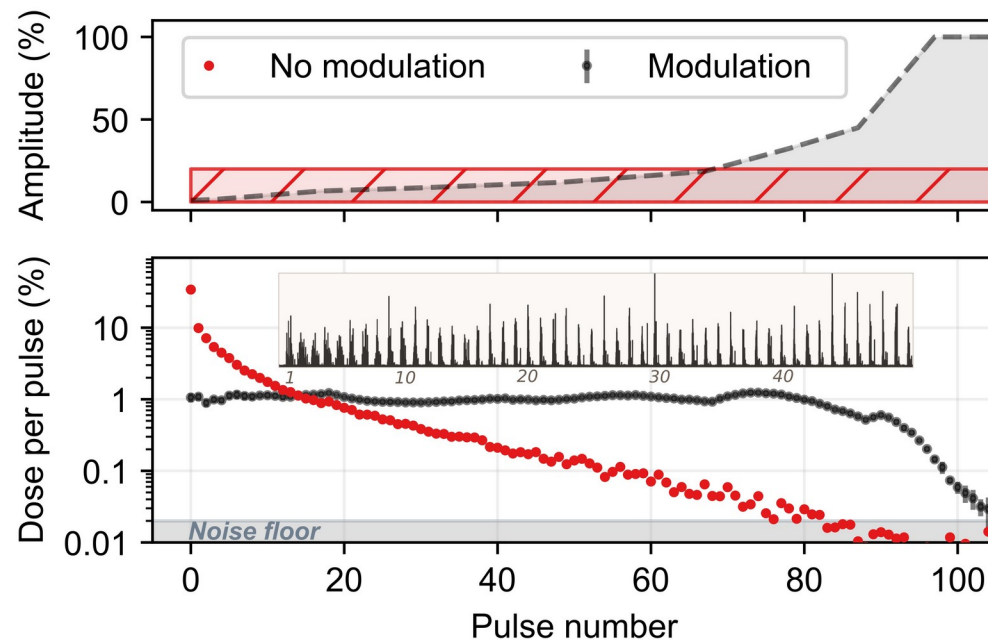
Flexibility of RF KO

- Pulse frequency: 250 Hz - 10 kHz
 - Duty cycle : 10-90%
 - Random pulse-to-pulse spacing
- Turn-off-dose is below 1 mGy

Amplitude modulation :

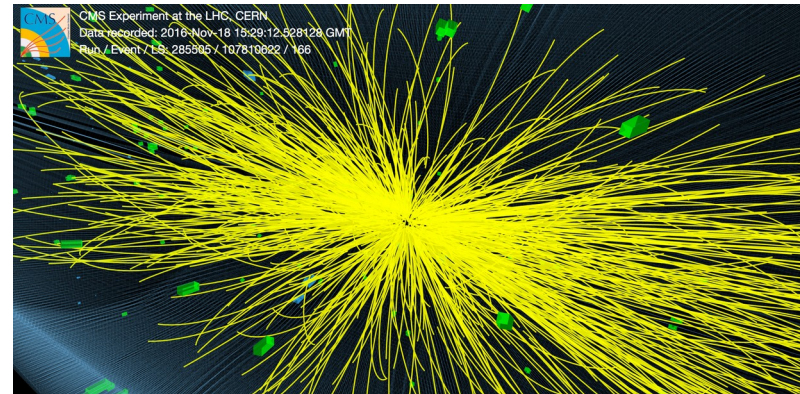
- ~80 RF KO pulses with uniform amplitude can be obtained

For biological / pre-clinical studies:
Combine everything into a prototype
FLASH dose-delivery system



Silicon Carbide Timing Detectors

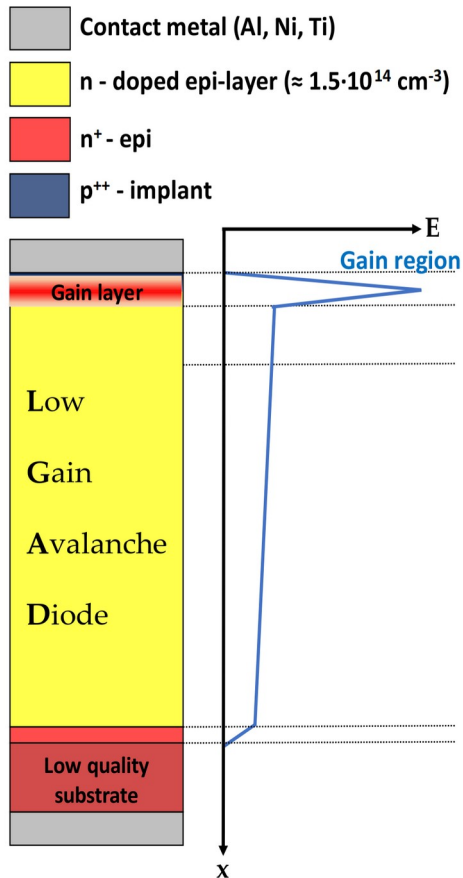
- Large effort in HEP towards fast and radiation hard timing detectors $\mathcal{O}(< 30\text{-}50 \text{ ps})$
- Application in ion imaging (ToF-iCT)
- SiC: fast drift velocity \rightarrow faster signals
- Need low-gain avalanche diodes (LGADs) to obtain sufficient SNR
- SiC-LGADs might surpass Si-LGADs



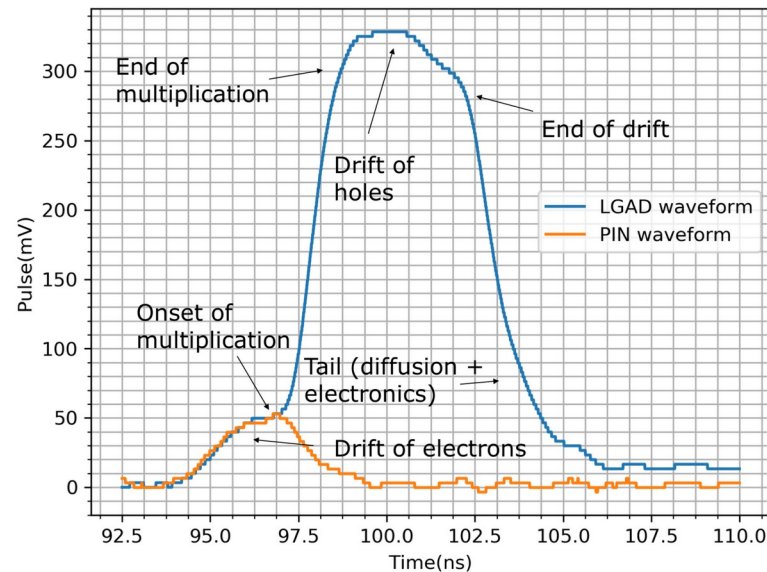
High multiplicity event in CMS

$$\sigma_{\text{Jitter}} \approx \frac{t_r}{S/N}$$

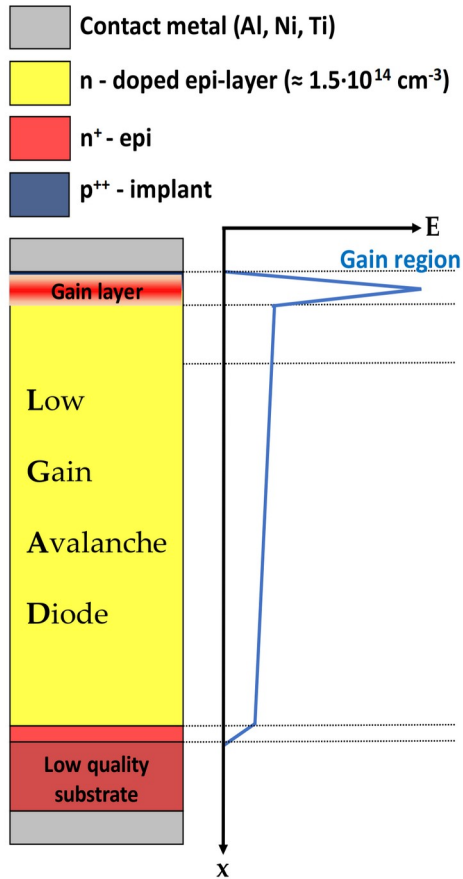
Silicon Carbide LGADs



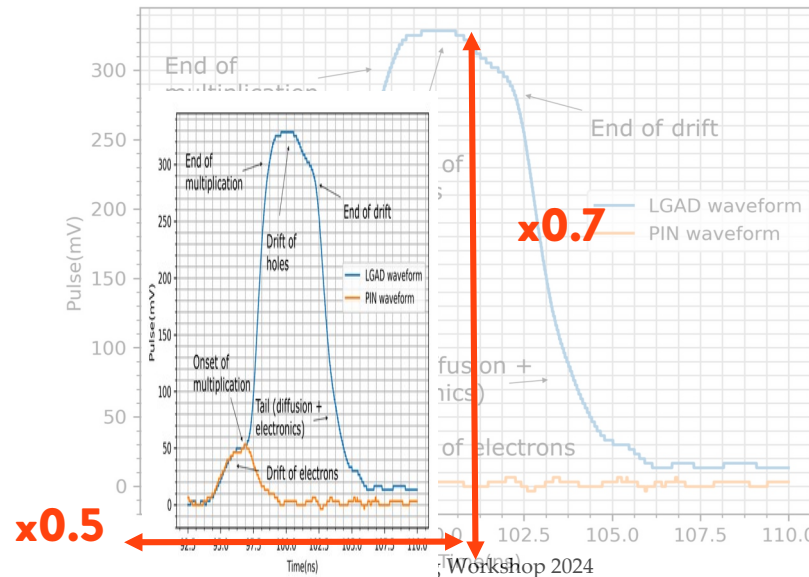
- LGAD maximal signal when all charge carriers have drifted to the gain layer (where they multiply)
- Worse risetime than planar sensors, but much better SNR



Silicon Carbide LGADs



- LGAD maximal signal when all charge carriers have drifted to the gain layer (where they multiply)
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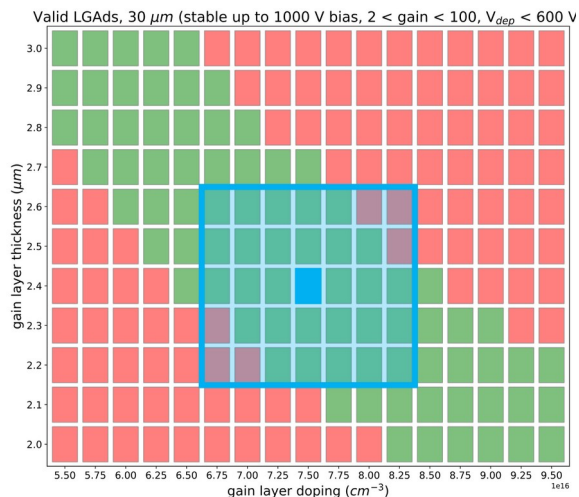


For SiC:

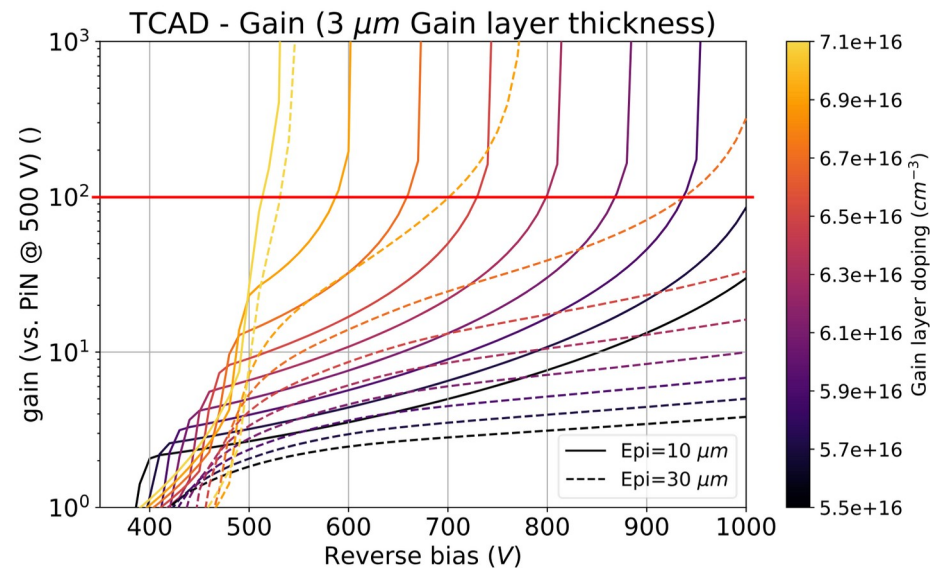
- ~ 30% smaller signals
- **But ~twice as fast**

SiC-LGAD Production

- Gain layer needs to be epitaxially grown, can not be implanted
- Ongoing project in the CERN RD50 (now DRD3) collaboration
- 10 6-inch wafers gain layer, wafer design by HEPHY
- Processing to start early 2025



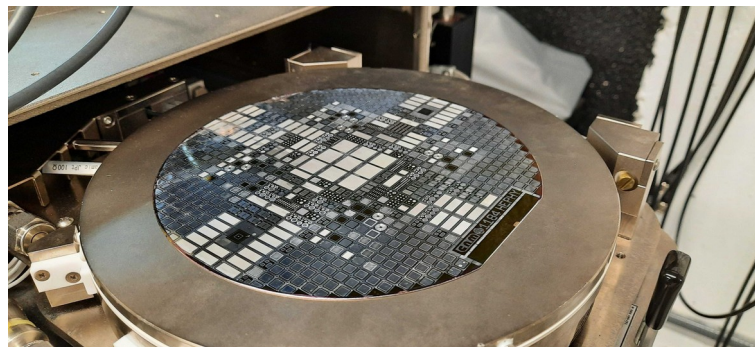
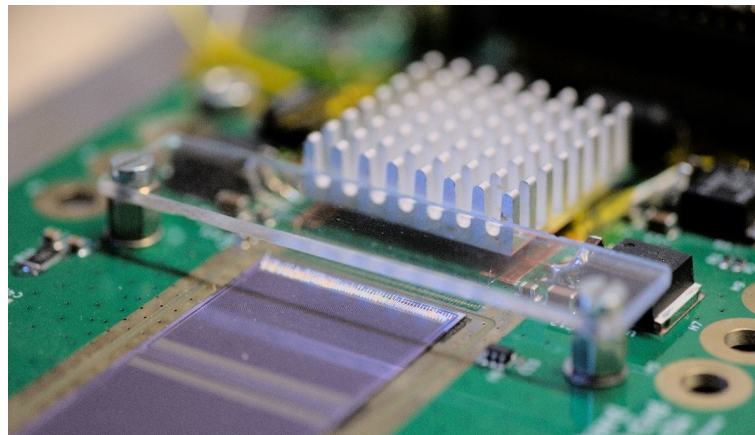
Gain layer doping study



Projected performance for different gain layer concentrations

Future Plans

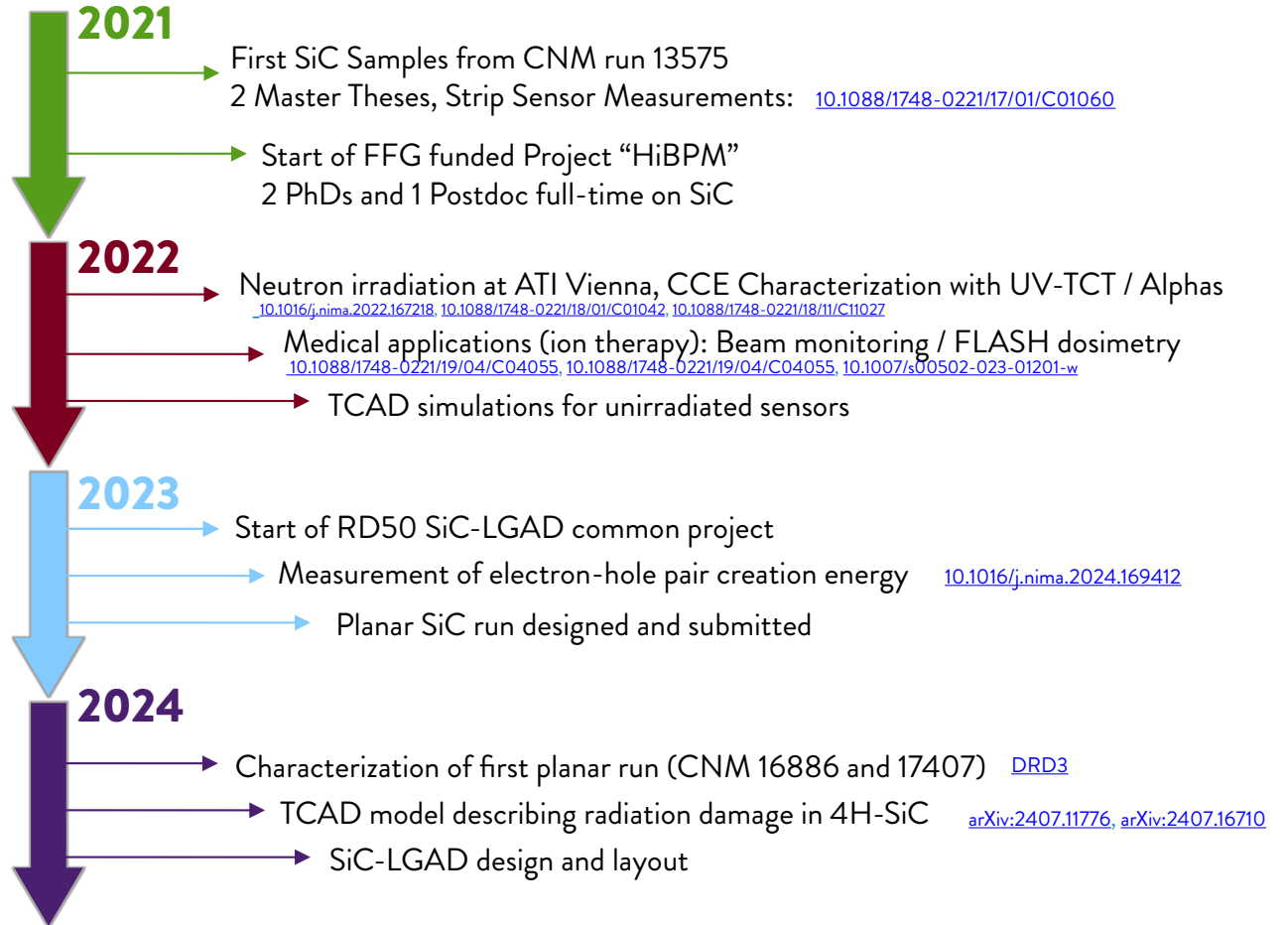
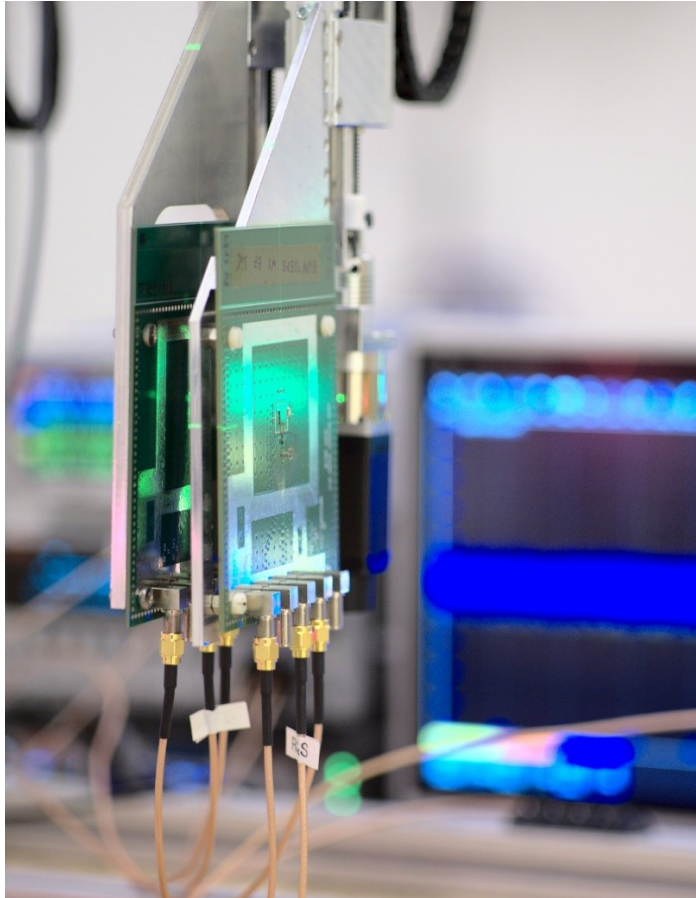
- Continue work on FLASH beams
- Study of SiC material parameters
- Beam monitor based on SiC strip detectors and COTS (FLASH compatible in the future!)
- SiC LGADs for timing / ToF
- SiC-MAPS in Fraunhofer SiC-CMOS process



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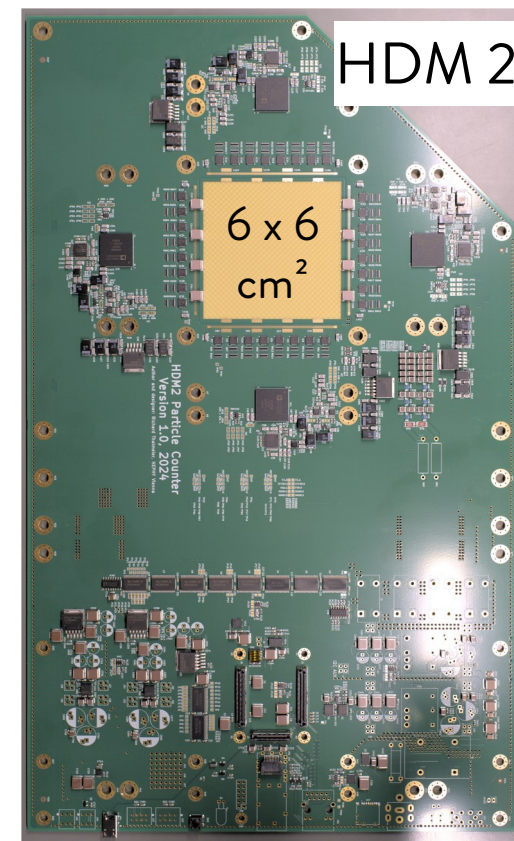
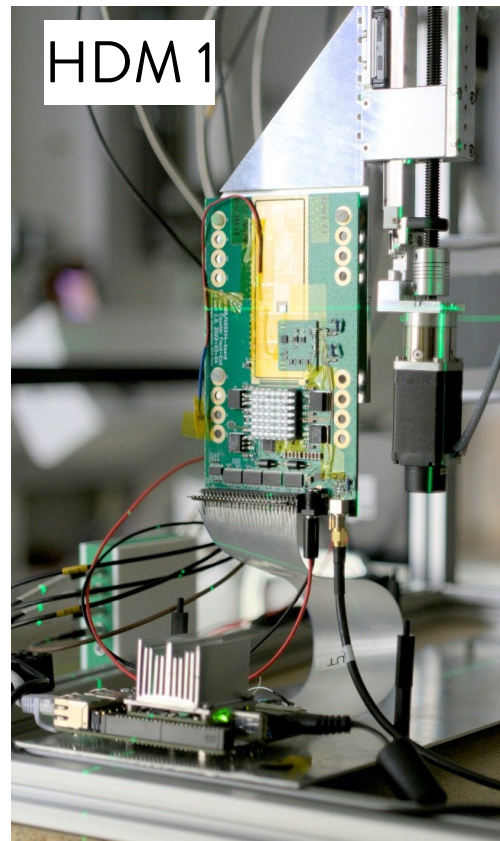
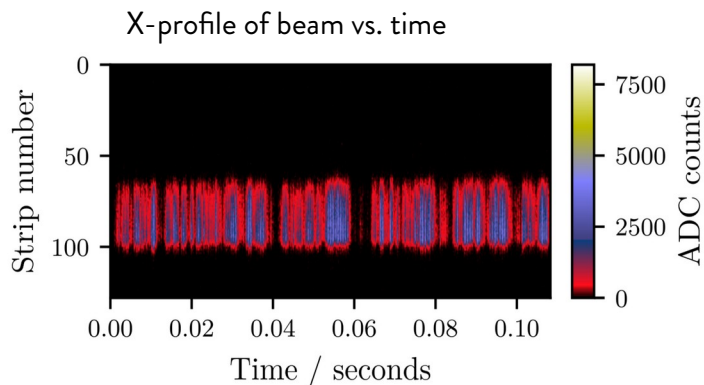
APPENDIX

HEPHY SiC Timeline



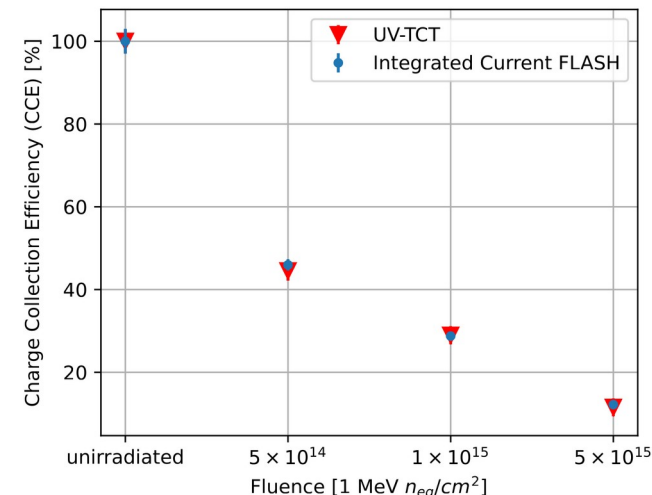
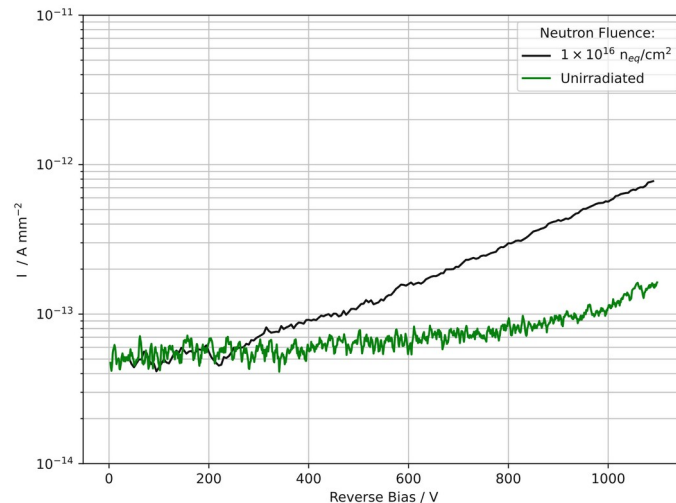
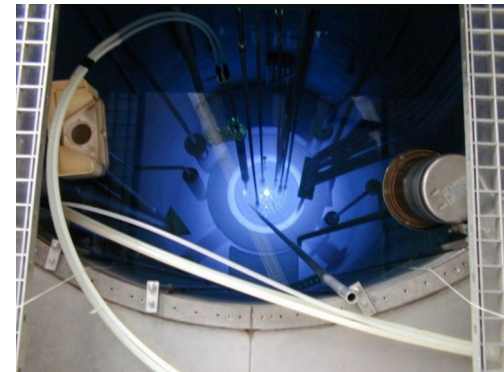
HiBPM Beam Monitor (HDM)

- Based on Analog Devices AD8488 (x-ray frontend chip) (off-the-shelf)
- 128 channels per IC, read-out at 37 kHz
- HDM1 : Prototype with 128 channels
- HDM2 : Demonstrator with 4 ICs, covering 6×6 cm² using daisy-chained SiC strip detectors
- Future FLASH compability: tunable gain / **attenuation** for each channel



SiC Radiation Hardness

- Irradiation at TRIGA MK II reactor at ATI Vienna
- Fluences up to $1 \times 10^{16} \text{ n}_{\text{eq}}/\text{cm}^2$, \mathcal{O} (CMS inner layers)
- Almost no increase in leakage current (still $< 1 \text{ pA}/\text{mm}^2$)
- Reduction in charge collection efficiency

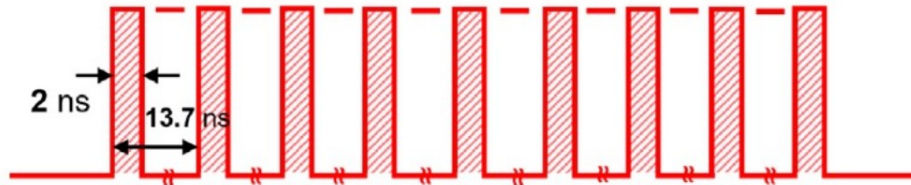


UHDR Pulses

protons $\dot{d} < 500 \text{ Gy/s}$

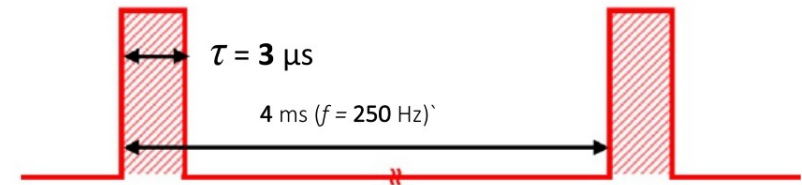
electrons

Isochronous cyclotron (quasi-continuous radiation)
($f=72.8 \text{ MHz}$, 2nd Harmonic)

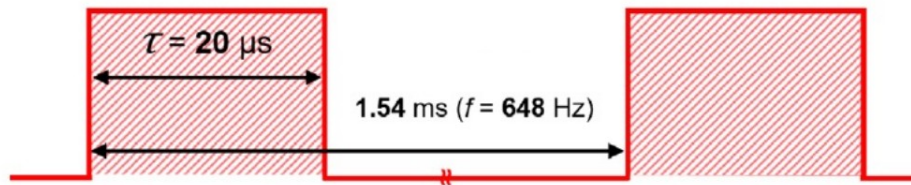


$\dot{d} < 100 \text{ kGy/s}$

Clinical LINAC for Radiotherapy (modified)

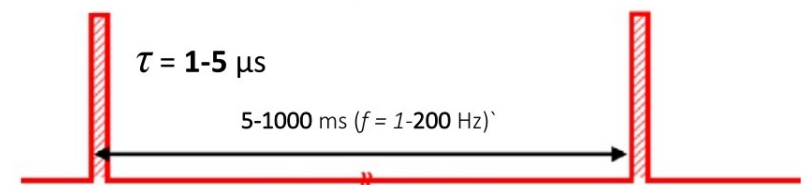


Synchrocyclotron (FLASH dose rate) $\dot{d} < 10 \text{ kGy/s}$



$\dot{d} < 5 \text{ MGy/s}$

Research LINAC for pre-clinical studies



F. Romano *et al.* Med. Phys. (2022)